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Substitute for form 1449B/PATENT

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

Filed: November 29, 2007

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Sheet 1 of 3

Complete if Known

Application Number	Unassigned
Filing Date	
First Named Inventor	Igor BARGATIN et al.
Group Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	049411-0340

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
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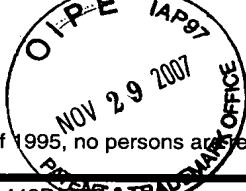
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		Application Number	Unassigned
Sheet		Filing Date	
2		First Named Inventor	Igor BARGATIN et al.
of		Group Art Unit	Unassigned
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		Attorney Docket Number	049411-0340

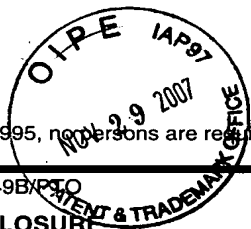
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First Named Inventor	Igor BARGATIN et al.
Group Art Unit	Unassigned
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Attorney Docket Number	049411-0340

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
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